Yiming Yu

List of Publications by Citations

81 papers	660 citations	14 h-index	22 g-index
94 ext. papers	922 ext. citations	2.6 avg, IF	4.15 L-index

#	Paper	IF	Citations
81	A 60-GHz OOK Receiver With an On-Chip Antenna in 90 nm CMOS. *IEEE Journal of Solid-State Circuits*, **2010**, 45, 1720-1731	5.5	87
80	. *IEEE Journal of Solid-State Circuits*, **2017**, 52, 2892-2904	5.5	56
79	Analysis and Design of Ultra-Wideband mm-Wave Injection-Locked Frequency Dividers Using Transformer-Based High-Order Resonators. *IEEE Journal of Solid-State Circuits*, **2018**, 53, 2177-2189	5.5	37
78	Scalable Transmission Line and Inductor Models for CMOS Millimeter-Wave Design. *IEEE Transactions on Microwave Theory and Techniques*, **2008**, 56, 2954-2962	4.1	37
77	A 60-GHz 19.8-mW Current-Reuse Active Phase Shifter With Tunable Current-Splitting Technique in 90-nm CMOS. *IEEE Transactions on Microwave Theory and Techniques*, **2016**, 64, 1572-1584	4.1	34
76	Analysis and Equivalent-Circuit Model for CMOS On-Chip Multiple Coupled Inductors in the Millimeter-Wave Region. *IEEE Transactions on Electron Devices*, **2015**, 62, 3957-3964	2.9	29
75	Analysis and Design of Inductorless Wideband Low-Noise Amplifier With Noise Cancellation Technique. *IEEE Access*, **2017**, 5, 9389-9397	3.5	24
74	A Broadband and Equivalent-Circuit Model for Millimeter-Wave On-Chip M:N Six-Port Transformers and Baluns. *IEEE Transactions on Microwave Theory and Techniques*, **2015**, 63, 3109-3121	4.1	22
73	An Injection-Current-Boosting Locking-Range Enhancement Technique for Ultra-Wideband mm-Wave Injection-Locked Frequency Triplers. *IEEE Transactions on Microwave Theory and Techniques*, **2019**, 67, 3174-3186	4.1	21
72	Fully Coupled Multiphysics Simulation of Crosstalk Effect in Bipolar Resistive Random Access Memory. *IEEE Transactions on Electron Devices*, **2017**, 64, 3647-3653	2.9	19
71	A New Six-Port Transformer Modeling Methodology Applied to 10-dBm 60-GHz CMOS ASK Modulator Designs. *IEEE Transactions on Microwave Theory and Techniques*, **2010**, 58, 297-309	4.1	18
70	A 62-90 GHz High Linearity and Low Noise CMOS Mixer Using Transformer-Coupling Cascode Topology. *IEEE Access*, **2018**, 6, 19338-19344	3.5	17
69	A CMOS K-Band 6-bit Attenuator With Low Phase Imbalance for Phased Array Applications. *IEEE Access*, **2017**, 5, 19657-19661	3.5	17
68	A 256-QAM 39 GHz Dual-Channel Transceiver Chipset with LTCC Package for 5G Communication in 65 nm CMOS **2018**,		16
67	Analysis and Design of CMOS Doherty Power Amplifier Based on Voltage Combining Method. *IEEE Access*, **2017**, 5, 5001-5012	3.5	13
66	Blind Nonlinear Self-Interference Cancellation for Wireless Full-Duplex Transceivers. *IEEE Access*, **2018**, 6, 37725-37737	3.5	13
65	. *IEEE Access*, **2018**, 6, 10131-10138	3.5	12

64	An Improved Ultrawideband Open-Short De-Embedding Method Applied up to 220 GHz. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2018**, 8, 269-276	1.7	11
63	An Ultralow Phase Noise Eight-Core Fundamental 62-to-67-GHz VCO in 65-nm CMOS. *IEEE Microwave and Wireless Components Letters*, **2019**, 29, 125-127	2.6	11
62	A 220-GHz Compact Equivalent Circuit Model of CMOS Transistors. *IEEE Microwave and Wireless Components Letters*, **2017**, 27, 651-653	2.6	9
61	An Improved RF MOSFET Model Accounting Substrate Coupling Among Terminals. *IEEE Microwave and Wireless Components Letters*, **2018**, 28, 138-140	2.6	9
60	A 60-GHz Variable Gain Phase Shifter With 14.8-dB Gain Tuning Range and 6-Bit Phase Resolution Across 25 °C to 110 °C. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 2371-2385	4.1	8
59	A 19.5% Efficiency 51-73-GHz High-Output Power Frequency Doubler in 65-nm CMOS. *IEEE Microwave and Wireless Components Letters*, **2019**, 29, 818-821	2.6	8
58	A Wideband Model for On-Chip Interconnects With Different Shielding Structures. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2017**, 7, 1702-1712	1.7	7
57	. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 756-773	4.1	7
56	A 37-40-GHz Low-Phase-Imbalance CMOS Attenuator With Tail-Capacitor Compensation Technique. *IEEE Transactions on Circuits and Systems I: Regular Papers*, **2020**, 67, 3400-3409	3.9	6
55	. *IEEE Access*, **2020**, 8, 29311-29318	3.5	6
54	A 21-to-41-GHz High-Gain Low Noise Amplifier With Triple-Coupled Technique for Multiband Wireless Applications. *IEEE Transactions on Circuits and Systems II: Express Briefs*, **2021**, 68, 1857-1861	3.5	6
53	Fully Coupled Electrothermal Simulation of Large RRAM Arrays in the Thermal-House *IEEE Access* , **2019**, 7, 3897-3908	3.5	5
52	An Equivalent Circuit Model With Current Return Path Effects for ON-Chip Interconnect up to 80 GHz. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2015**, 5, 1320-1330	1.7	5
51	A K-Band Frequency Tripler Using Transformer-Based Self-Mixing Topology With Peaking Inductor. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 68, 1688-1696	4.1	5
50	A 51.5 - 64.5 GHz Active Phase Shifter Using Linear Phase Control Technique With 1.4 Phase resolution in 65-nm CMOS **2019**,		4
49	A 62-85-GHz High Linearity Upconversion Mixer With 18-GHz IF Bandwidth. *IEEE Microwave and Wireless Components Letters*, **2019**, 29, 219-221	2.6	4
48	An Improved Small-Signal Equivalent Circuit Model Considering Channel Current Magnetic Effect. *IEEE Microwave and Wireless Components Letters*, **2018**, 28, 804-806	2.6	4
47	Characterization and Modeling of Multiple Coupled Inductors Based on On-Chip Four-Port Measurement. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2014**, 4, 1696-1704	1.7	4

46	**2017**,		4
45	CMOS 90 nm multi-bias transistor model Up to 66 GHz **2017**,		4
44	A 5-Gb/s 66 dB CMOS Variable-Gain Amplifier With Reconfigurable DC-Offset Cancellation for Multi-Standard Applications. *IEEE Access*, **2018**, 6, 54139-54146	3.5	4
43	Analysis and design of transformer-based CMOS ultra-wideband millimeter-wave circuits for wireless applications: a review. *Frontiers of Information Technology and Electronic Engineering*, **2020**, 21, 97-115	2.2	3
42	A 24 GHz enhanced neutralized cascode LNA with 4.7 dB NF and 19.8 dB gain. *IEICE Electronics Express*, **2018**, 15, 20180464-20180464	0.5	3
41	A 44 To 64 GHz Broadband 90° Hybrid Doherty PA With Quasi Non-Foster Tuner in 0.13 μm SiGe. *IEEE Microwave and Wireless Components Letters*, **2021**, 31, 760-763	2.6	3
40	An Improved Surface Potential-Based High-Order Channel Length Modulation Model **2019**,		3
39	Multi-bias Small Signal Circuit Model for FinFET Transistors **2019**,		3
38	RF CMOS Transistor Equivalent Circuit Model up to 66 GHz **2018**,		3
37	A CMOS Ku-band receiver chain for phased array system. *IEICE Electronics Express*, **2018**, 15, 20180888-20180888	0.5	3
36	. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 3989-4000	4.1	3
35	A Ka-Band CMOS Variable Gain Amplifier with High Gain Resolution and Low Phase Variation **2020**,		2
34	A 68.5~90 GHz High-Gain Power Amplifier With Capacitive Stability Enhancement Technique in 0.13 μm SiGe BiCMOS. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 1-1	4.1	2
33	A 15-27 GHz Low Conversion Loss and High Isolation Resistive Ring Mixer for Direct Conversion Receiver **2019**,		2
32	A 10-mW 3.9-dB NF transformer-based V-band low-noise amplifier in 65-nm CMOS. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2576	1	2
31	An improved open-short equivalent circuit model for CMOS transistors de-embedding. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2589	1	2
30	An improved wideband equivalent circuit model for integrated spiral inductors in CMOS technology. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2640	1	2
29	A Wideband CMOS Frequency Quadrupler With Transformer-Based Tail Feedback Loop. *IEEE Transactions on Circuits and Systems II: Express Briefs*, **2021**, 68, 1153-1157	3.5	2

28	Analysis and Design of High-Harmonic-Rejection Multi-Ratio mm-Wave Frequency Multipliers. *IEEE Journal of Solid-State Circuits*, **2021**, 1-1	5.5	2
27	An Improved Surface-Potential-Based Model for MOSFETs Considering the Carrier Gaussian Distribution. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 68, 4082-4090	4.1	1
26	66 GHz bias-dependent equivalent circuit model for CMOS transistor based on 90 nanometers CMOS technology. *Microwave and Optical Technology Letters*, **2018**, 60, 1808-1812	1.2	1
25	High-Isolation CMOS T/R Switch Design Using a Two-Stage Equivalent Transmission Line Structure. *IEEE Access*, **2017**, 5, 22704-22712	3.5	1
24	A 60-GHz vector summing phase shifter with digital tunable current-splitting and current-reuse techniques in 90 nm CMOS **2015**,		1
23	A 33–41-GHz SiGe-BiCMOS Digital Step Attenuator With Minimized Unit Impedance Variation. *IEEE Transactions on Very Large Scale Integration (VLSI) Systems*, **2021**, 29, 568-579	2.6	1
22	A SiGe Power Amplifier With Double Gain Peaks Based on the Control of Stationary Points of Impedance Transformation. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 2279-2290	4.1	1
21	An Improved Large-Signal Equivalent Circuit Model for Partially Depleted Silicon-on-Insulator MOSFET. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 2972-2980	4.1	1
20	An Improved Small Signal Equivalent Circuit Modeling Based On 65nm CMOS Technology **2019**,		1
19	Differential low-loss T/R switch for phase array application in 0.18-μm CMOS technology. *IET Microwaves, Antennas and Propagation*, **2019**, 13, 813-818	1.6	1
18	A High Linearity Low Noise Amplifier for 5G Front-End Modules **2019**,		1
17	Millimeter wave balun design and optimization based on compensation matching capacitors and active S parameter. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2644	1	1
16	A millimeter-wave scalable small signal model of RF CMOS transistor against number of fingers. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2608	1	1
15	An improved 220-GHz RF CMOS compact equivalent circuit model considering magnetic coupling effect. *Microwave and Optical Technology Letters*, **2021**, 63, 1048-1053	1.2	1
14	A 8.5 to 11.6 GHz digitally controlled variable gain amplifier with 15-dB gain range and 1-dB step. *Microwave and Optical Technology Letters*, **2021**, 63, 411-416	1.2	1
13	A package-level wideband driver amplifier with 134% fractional bandwidth. *IEICE Electronics Express* , **2018**, 15, 20180179-20180179	0.5	1
12	An Empirical Nonlinear Capacitance Model for SOI Transistor **2018**,		1
11	Hexahedron-Based Control Volume Finite Element Method for Fully Coupled Nonlinear Drift-Diffusion Transport Equations in Semiconductor Devices. *IEEE Transactions on Microwave Theory and Techniques*, **2022**, 1-1	4.1	1

10	A Q-band CMOS LNA exploiting transformer feedback and noise-cancelling. *Science China Information Sciences*, **2015**, 58, 1-10	3.4	0
9	A Ka-Band CMOS Phase-Invariant and Ultralow Gain Error Variable Gain Amplifier With Active Cross-Coupling Neutralization and Asymmetric Capacitor Techniques. *IEEE Transactions on Microwave Theory and Techniques*, **2022**, 70, 85-100	4.1	0
8	A Harmonic-Tuned VCO With an Intrinsic-High-Q F23 Inductor in 65-nm CMOS. *IEEE Microwave and Wireless Components Letters*, **2020**, 30, 981-984	2.6	0
7	A 21.5 ~ 25 GHz 7-bit phase shifter with passive vector-sum topology. *Microwave and Optical Technology Letters*, **2021**, 63, 1652-1656	1.2	0
6	A Wide-Band Divide-By-2 Injection-Locked Frequency Divider Based on Distributed Dual-Resonance Tank. *Electronics (Switzerland)*, **2022**, 11, 506	2.6	
5	Dual-beam and dual-mode circularly polarized antenna based on substrate integrated waveguide technology. *Microwave and Optical Technology Letters*, **2021**, 63, 2882-2887	1.2	
4	A 27.5-43.5 GHz 65-nm CMOS up-conversion mixer with 0.42 dBm OP1dB for 5G applications. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2550	1	
3	A 3-GHz Inverse-Coupled Current-Reuse VCO Implemented by 1:1 Transformer. *IEEE Microwave and Wireless Components Letters*, **2022**, 1-3	2.6	
2	A Ku-Band Eight-Element Phased-Array Transmitter With Built-in Self-Test Capability in 180-nm CMOS Technology. *IEEE Transactions on Very Large Scale Integration (VLSI) Systems*, **2022**, 1-12	2.6	
1	Temperature-Dependent Threshold Voltage Extraction of FinFETs Using Noise Measurements. *IEEE Transactions on Microwave Theory and Techniques*, **2022**, 1-1	4.1	